



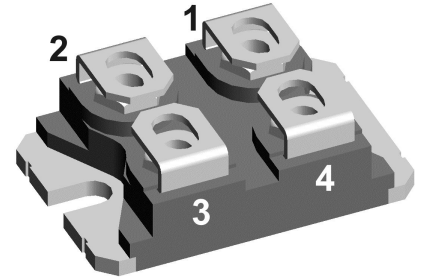
# FRED

$V_{RRM} = 400\text{ V}$   
 $I_{FAV} = 2 \times 30\text{ A}$   
 $t_{rr} = 35\text{ ns}$

Fast Recovery Epitaxial Diode  
 Low Loss and Soft Recovery  
 Parallel legs

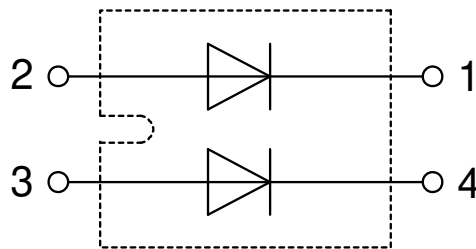
Part number

**DSEI2x31-04C**



Backside: isolated

E72873



### Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

### Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

### Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

### Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).

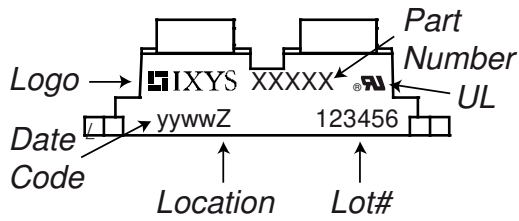


Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM}$	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			400	V	
$V_{RRM}$	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			400	V	
$I_R$	reverse current, drain current	$V_R = 400 V$	$T_{VJ} = 25^{\circ}C$		100	$\mu A$	
		$V_R = 320 V$	$T_{VJ} = 125^{\circ}C$		7	mA	
$V_F$	forward voltage drop	$I_F = 30 A$	$T_{VJ} = 25^{\circ}C$		1.51	V	
		$I_F = 60 A$			1.68	V	
		$I_F = 30 A$	$T_{VJ} = 150^{\circ}C$		1.34	V	
		$I_F = 60 A$			1.60	V	
$I_{FAV}$	average forward current	$T_C = 90^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}C$		30	A	
$V_{FO}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		1.10	V	
$r_F$	slope resistance				7.9	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				1.2	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.10		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		105	W	
$I_{FSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$		300	A	
$C_J$	junction capacitance	$V_R = 400 \text{ V}$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		27	pF	
$I_{RM}$	max. reverse recovery current	} $I_F = 37 \text{ A}; V_R = 350 \text{ V}$ $-di_F/dt = 200 \text{ A}/\mu\text{s}$	$T_{VJ} = 25^{\circ}C$		5.5	A	
			$T_{VJ} = 100^{\circ}C$		9	A	
$t_{rr}$	reverse recovery time		$T_{VJ} = 25^{\circ}C$		80	ns	
			$T_{VJ} = 100^{\circ}C$		150	ns	



Package SOT-227B (minibloc)				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$I_{RMS}$	RMS current	per terminal			70	A	
$T_{VJ}$	virtual junction temperature		-40		150	°C	
$T_{op}$	operation temperature		-40		125	°C	
$T_{stg}$	storage temperature		-40		150	°C	
<b>Weight</b>				30		g	
$M_D$	mounting torque		1.1		1.5	Nm	
$M_T$	terminal torque		1.1		1.5	Nm	
$d_{Spp/ App}$	creepage distance on surface   striking distance through air	terminal to terminal	10.5	3.2		mm	
$d_{Spb/ Apb}$		terminal to backside	8.6	6.8		mm	
$V_{ISOL}$	isolation voltage	t = 1 second			3000	V	
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		2500	V	

**Product Marking**



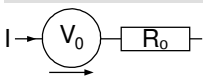
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI2x31-04C	DSEI2x31-04C	Tube	10	456403

Similar Part	Package	Voltage class
DSEI2x30-04C	SOT-227B (minibloc)	400

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150^\circ\text{C}$

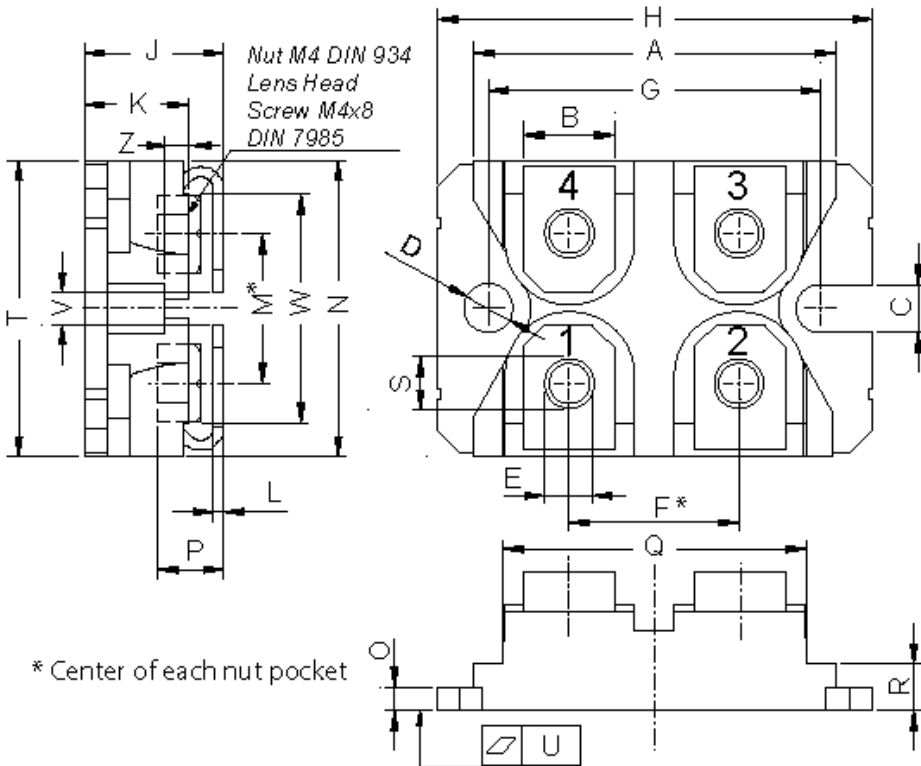


**Fast Diode**

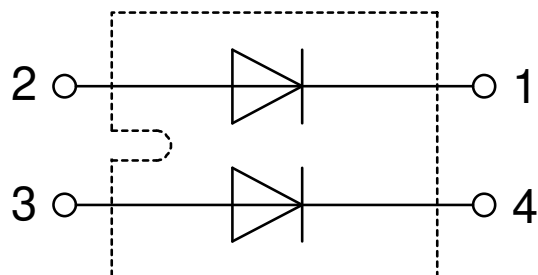
$V_{0 \max}$	threshold voltage	1.1	V
$R_{0 \max}$	slope resistance *	6	mΩ



**Outlines SOT-227B (minibloc)**



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



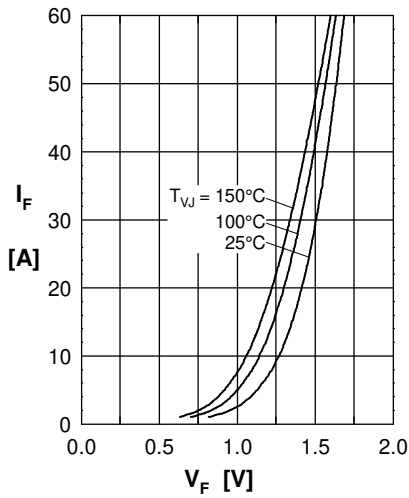
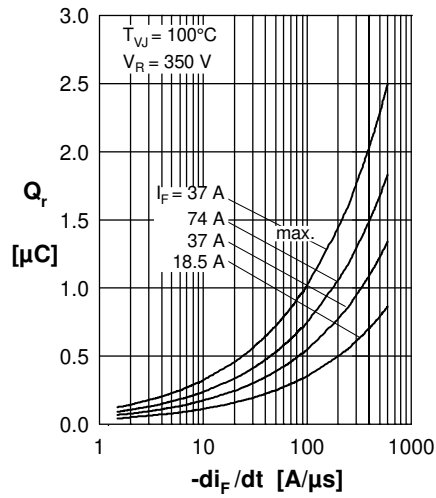
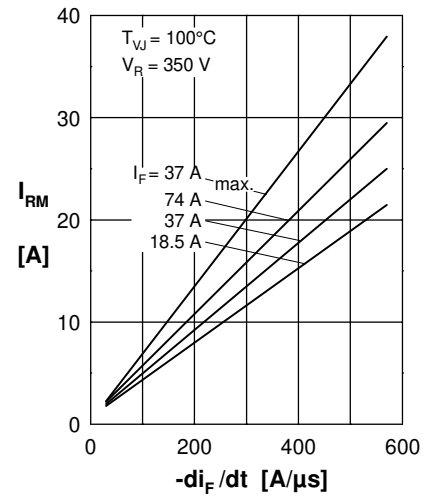
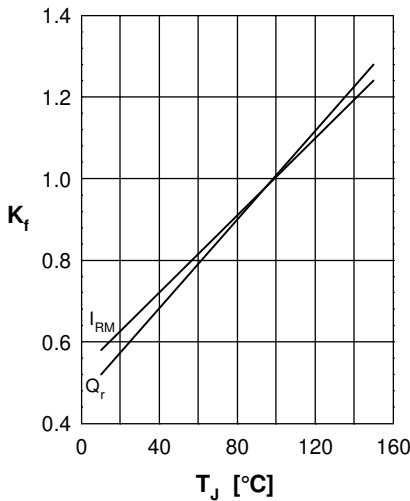
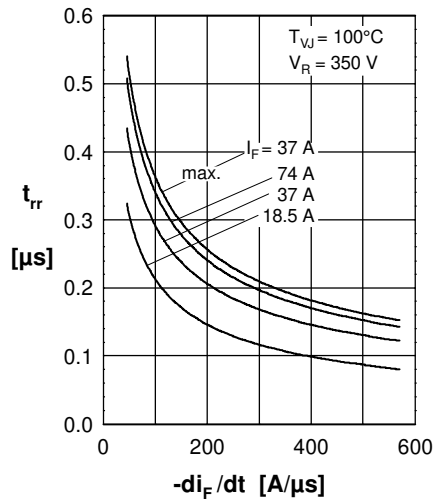
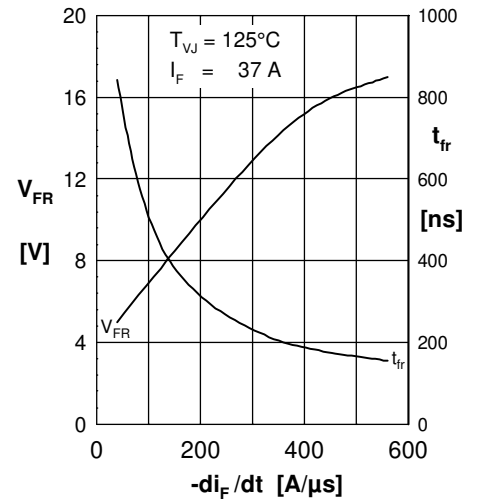
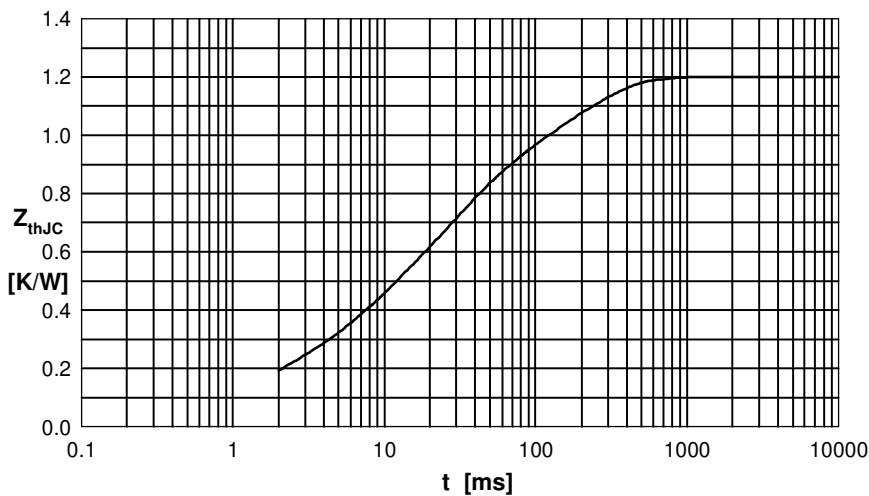
**Fast Diode**

 Fig. 1 Forward current  $I_F$  versus max. forward voltage drop  $V_F$ 

 Fig. 2 Typ. reverse recov. charge  $Q_r$  versus  $-di_F/dt$ 

 Fig. 3 Typ. peak reverse current  $I_{RM}$  versus  $-di_F/dt$ 

 Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$ 

 Fig. 5 Typ. recovery time  $t_{rr}$  versus  $-di_F/dt$ 

 Fig. 6 Typ. peak forward voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_F/dt$ 


Fig. 7 Transient thermal impedance junction to case

 Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.180	0.0050
2	0.020	0.0600
3	0.100	0.0010
4	0.400	0.1700
5	0.500	0.0230